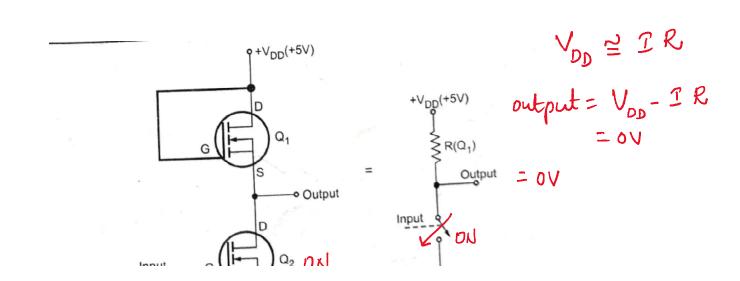
## NMOS Logic Family

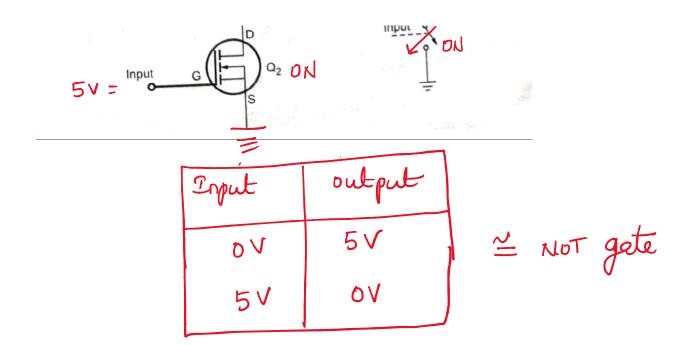
Vas	Lomn
ΟV	off
5√	ON

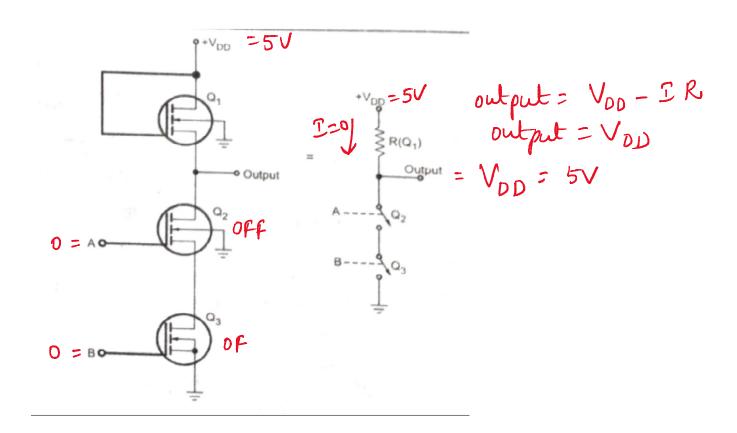
Table 6.9 summarizes the operation of NMOS inverter

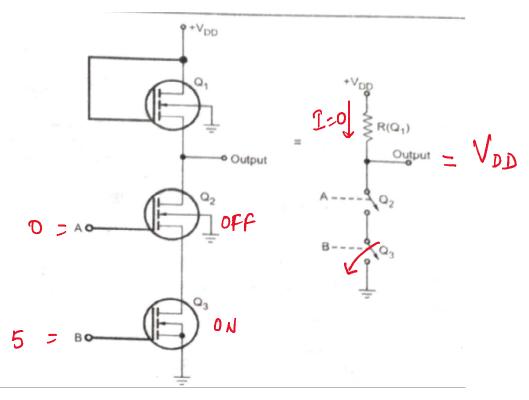
ラ

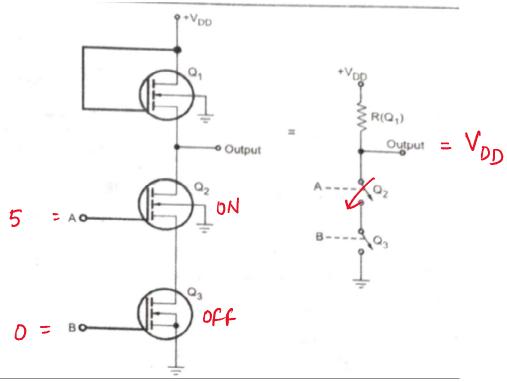
V <sub>IN</sub> (VGS)	Q <sub>2</sub>	$V_0 = \overline{V_{1N}}$	
0 V (logic 0)	OFF	+ 5 V (logic 1)	
5 V (logic 1)	ON	0 V (logic 0)	Dran
	• +V <sub>DD</sub> (+5V)	Gate	Drain Substate
G E	100KA I=	+V <sub>DD</sub> (+5V)  R(Q <sub>1</sub> )  Output	Sodice In R
Input G	Output DIKA Q <sub>2</sub> OFF	Input = VDD	0
	The second second		

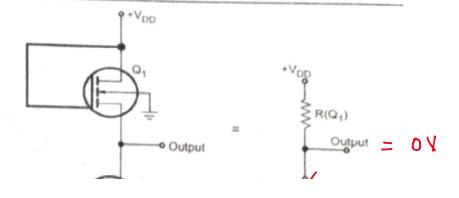


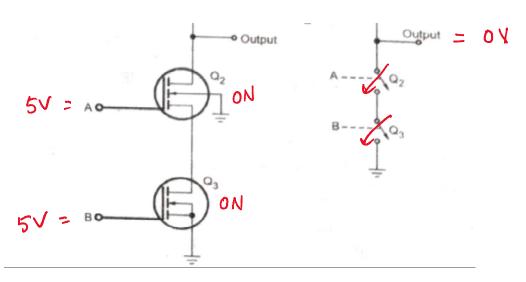












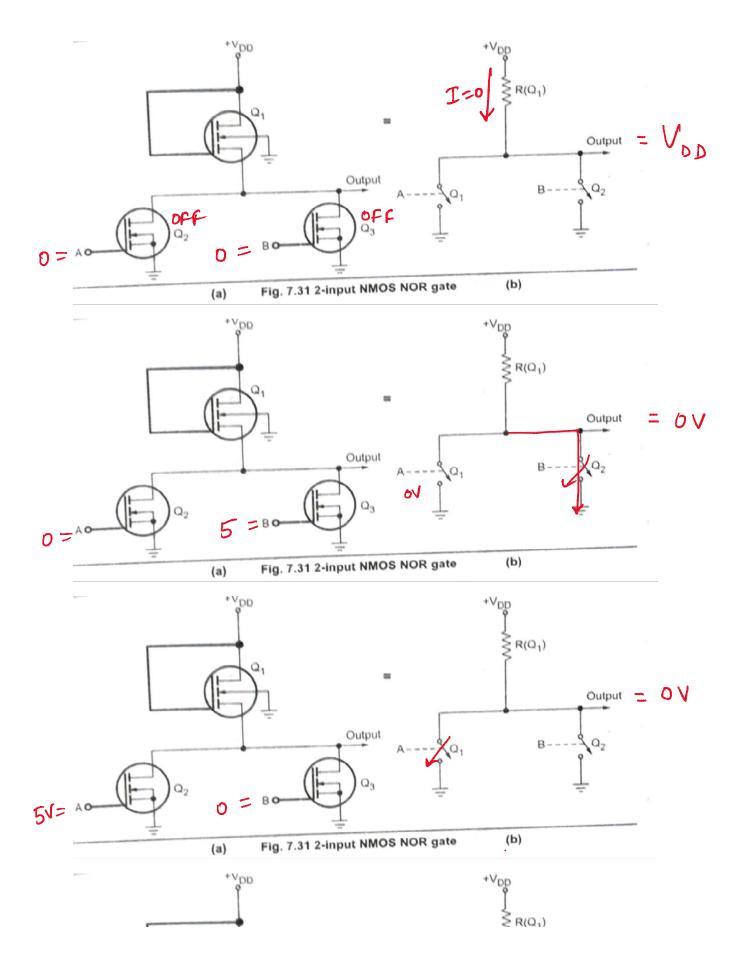
A	В	output		
0	0	5V		
0	5	5V	7	WAND
5	ס	5 V		
5	15	OV		

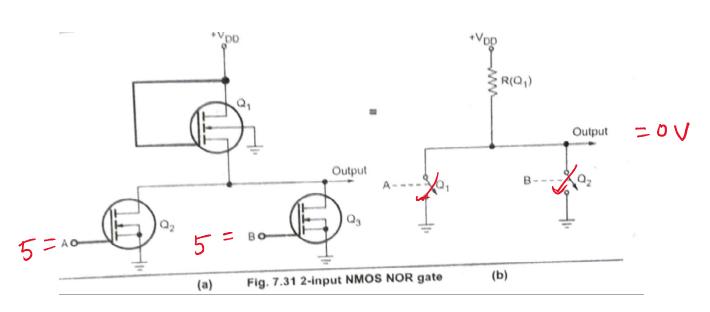
Table 7.11 summarizes the operation of NMOS NAND gate

A	В	Q <sub>2</sub>	$Q_3$	$V_{o} = \widetilde{AB}$
0	()	OFF	OFF	1
0	1	OFF	ON	1
1	0	ON	OFF	1
1	1	ON	ON	0

Table 7.11

## **NMOS NOR GATE**





1			
A	B	output	
0	0	5∨	
٥	5	0	= NOR, gate
5	٥	σ	= NOR gate
5	5	0	

Table 7.12 summarizes the operation of NMOS NOR gate.

10 7 7 10 0 11	В	Q <sub>2</sub>	Q <sub>3</sub>	V <sub>o</sub> ≈A + B
A	0	OFF	OFF	1
()	paragicatus propries condition de la const	OFF	ON	0
()	AND RESIDENCE OF STREET, SAME PARTY CONTRACT.	ON	OFF	0
proposition in a manufacture company of	A STATE OF THE PARTY OF T	ON	ON	0

Table 7.12

## Characteristics of NMOS

Operating speed: Low operating speed with propagation delay time around 50ns. This is because

it has high output resistance, very high input resistance and reasonably high

input capacitance.

Noise Margin:

Typically 1.5 V

Fan out:

Typically 30

Power drain:

Less, around 0.1 mW per gate.